

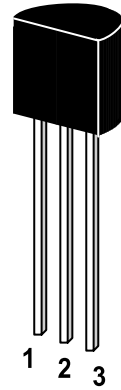
MPSA 92 / 93

PNP Silicon Expitaxial Planar Transistor

for high voltage switching and amplifier applications.

The transistor is subdivided into one group according to its DC current gain. As complementary type the NPN transistor MPSA 42 and MPSA 43 are recommended.

On special request, these transistors can be manufactured in different pin configurations.

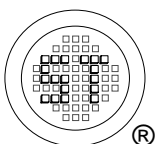


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

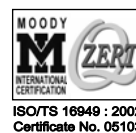
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value		Unit
		MPSA 92	MPSA 93	
Collector Base Voltage	$-V_{CBO}$	300	200	V
Collector Emitter Voltage	$-V_{CEO}$	300	200	V
Emitter Base Voltage	$-V_{EBO}$	5		V
Collector Current	$-I_C$	500		mA
Total Device Dissipation @ $T_a=25^\circ\text{C}$	P_{tot}	625		mW
Derate above 25°C		5		mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_c=25^\circ\text{C}$	P_{tot}	1.5		W
Derate above 25°C		12		mW/ $^\circ\text{C}$
Junction Temperature	T_j	150		$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150		$^\circ\text{C}$



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ISO/TS 16949 : 2002
Certificate No. 05103

ISO 14001:2004
Certificate No. 7116

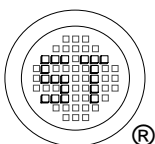
ISO 9001:2000
Certificate No. 0506098

Dated : 16/06/2004

MPSA 92 / 93

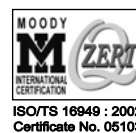
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-I_C=1\text{mA}$, $-V_{CE}=10\text{V}$ at $-I_C=10\text{mA}$, $-V_{CE}=10\text{V}$ at $-I_C=30\text{mA}$, $-V_{CE}=10\text{V}$		h_{FE}	25	-	-	-
		h_{FE}	40	-	-	-
		h_{FE}	25	-	-	-
Emitter Cutoff Current at $-V_{EB}=3\text{V}$		$-I_{EBO}$	-	-	0.1	μA
Collector Cutoff Current at $-V_{CB}=200\text{V}$ $-V_{CB}=160\text{V}$	MPSA 92	$-I_{CBO}$	-	-	0.25	μA
	MPSA 93	$-I_{CBO}$	-	-	0.25	μA
Collector Base Breakdown Voltage at $-I_C=100\mu\text{A}$	MPSA 92	$-V_{(BR)CBO}$	300	-	-	V
	MPSA 93	$-V_{(BR)CBO}$	200	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	MPSA 92	$-V_{(BR)CEO}$	300	-	-	V
	MPSA 93	$-V_{(BR)CEO}$	200	-	-	V
Emitter Base Breakdown Voltage at $-I_E=100\mu\text{A}$		$-V_{(BR)EBO}$	5	-	-	V
Collector Saturation Voltage at $-I_C=20\text{mA}$, $-I_B=2\text{mA}$		$-V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage at $-I_C=20\text{mA}$, $-I_B=2\text{mA}$		$-V_{BE(sat)}$	-	-	0.9	V
Gain Bandwidth Product at $-I_C=10\text{mA}$, $-V_{CE}=20\text{V}$, $f=100\text{MHz}$		f_T	50	-	-	MHz
Collector Output Capacitance at $-V_{CB}=20\text{V}$, $f=1\text{MHz}$	MPSA 92	C_{ob}	-	-	6	pF
	MPSA 93	C_{ob}	-	-	8	pF



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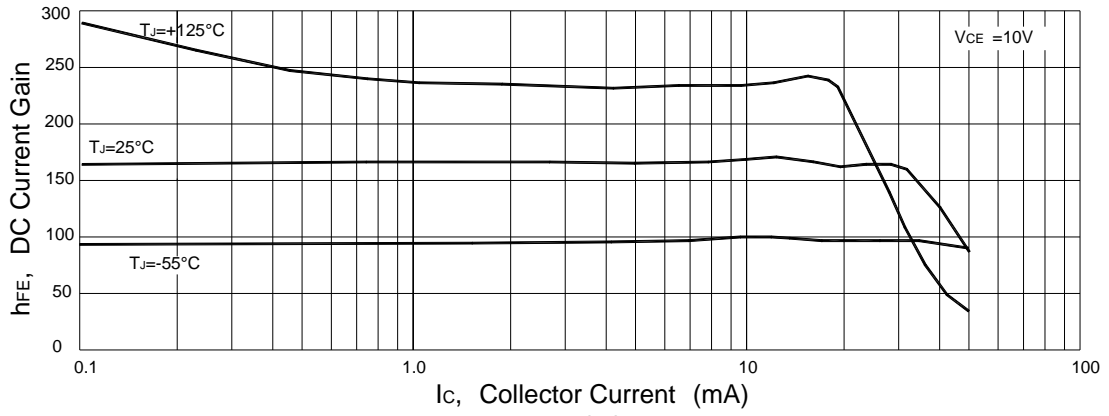


Figure 1. DC Current Gain

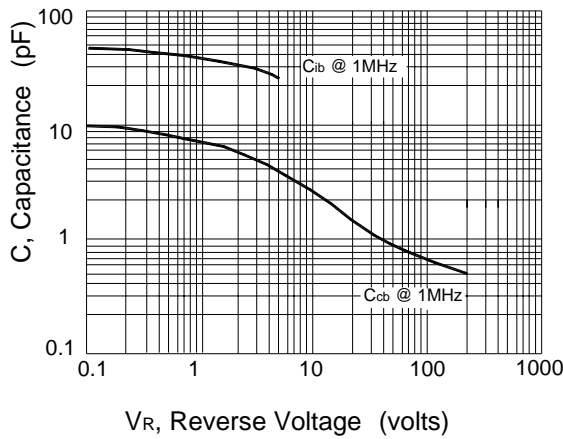


Figure 2. Capacitance

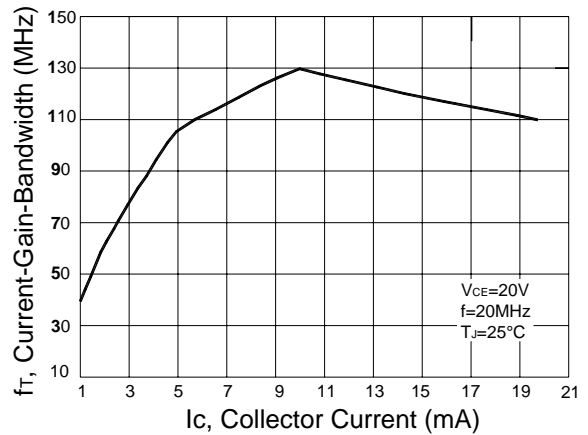
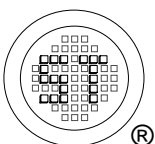


Figure 3. Current-Gain-Bandwidth



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